

$$I_{F(AV)} = 0.5\text{Amp}$$

$$V_R = 40\text{V}$$

#### Major Ratings and Characteristics

Characteristics	Value	Units
$I_{F(AV)}$ (DC)	0.5	A
$V_{RRM}$	40	V
$I_{FSM}$ @ $t_p = 10\text{ms}$ sine	6.0	A
$V_F$ @ $0.5\text{Apk}$ , $T_J = 100^\circ\text{C}$	0.42	V
$T_J$ range	- 65 to 150	$^\circ\text{C}$

#### Description/ Features

This Schottky diode is ideally suited for low voltage, high frequency operation, as freewheeling and polarity protection. Small size of the package allows proper use in application where compact size is critical, fitting also the GSM and PCMCIA requirement.

- Surface mountable
- Very low forward voltage drop
- Extremely fast switching
- Negligible switching losses
- Guard ring for enhanced ruggedness and long term reliability

#### Case Styles



SOD123

### Voltage Ratings

Part number	Value
V <sub>R</sub> Max. DC Reverse Voltage (V)	40
V <sub>RWM</sub> Max. Working Peak Reverse Voltage (V)	

### Absolute Maximum Ratings

Parameters	Value	Units	Conditions
I <sub>F</sub> Forward Current	0.5	A	DC, T <sub>L</sub> = 122°C
I <sub>FSM</sub> Max. Peak One Cycle Non-Repetitive Surge Current, @ T <sub>J</sub> = 25°C	50	A	5μs Sine or 3μs Rect. pulse
	6.0	A	10ms Sine or 6ms Rect. pulse

Following any rated load condition and with rated V<sub>RRM</sub> applied

### Electrical Specifications

Parameters	Value	Units	Conditions
V <sub>FM</sub> Max. Forward Voltage Drop (1)	0.480	V	@ 0.5A
	0.560	V	@ 1A
V <sub>FM</sub> Max. Forward Voltage Drop (1)	0.420	V	@ 0.5A
	0.520	V	@ 1A
I <sub>RM</sub> Max. Reverse Leakage Current	10	μA	V <sub>R</sub> = 20V
	5	mA	V <sub>R</sub> = 20V
	20	μA	V <sub>R</sub> = 40V
	13	mA	V <sub>R</sub> = 40V
C <sub>T</sub> Max. Junction Capacitance	60	pF	V <sub>R</sub> = 5V <sub>DC</sub> (test signal range 100KHz to 1Mhz), T <sub>J</sub> = 25°C
dv/dt Max. Voltage Rate of Change (Rated V <sub>R</sub> )	10000	V/μs	

(1) Pulse Width < 300μs, Duty Cycle < 2%

### Thermal-Mechanical Specifications

Parameters	Value	Units	Conditions
T <sub>J</sub> Max. Junction Temperature Range(*)	-65 to 150	°C	
T <sub>stg</sub> Max. Storage Temperature Range	-65 to 150	°C	
R <sub>th(j-l)</sub> Max. Thermal Resistance Junction to Lead	150	°C/W	Mounted on PC board FR4 with minimum pad size
R <sub>th(j-a)</sub> Max. Thermal Resistance Junction to Ambient	200	°C/W	1 inch square pad size (1 x 0.5 inch for each lead) on FR4 board
Wt Approximate Weight	0.012	g	
Case Style	SOD123		
Device Marking	CYWLC		

(\*)  $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

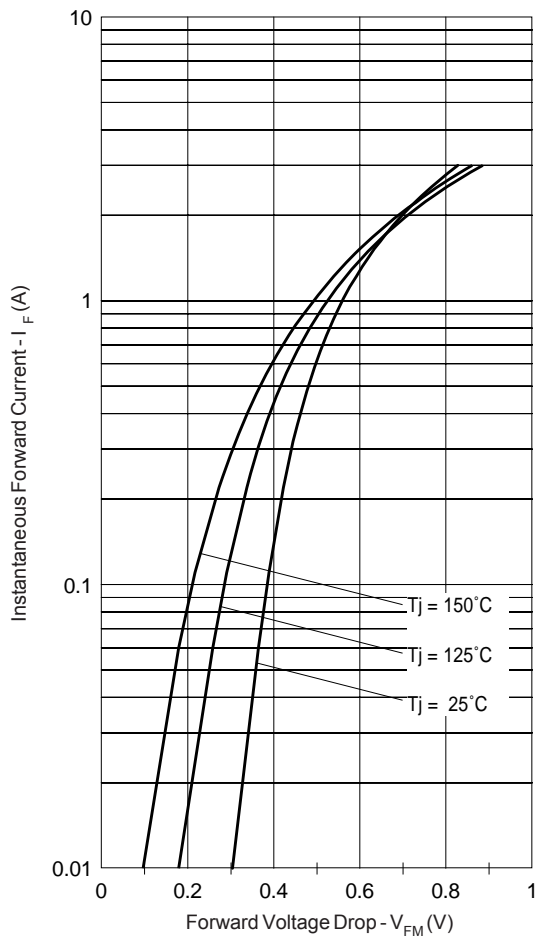


Fig. 1 - Max. Forward Voltage Drop Characteristics (Per Leg)

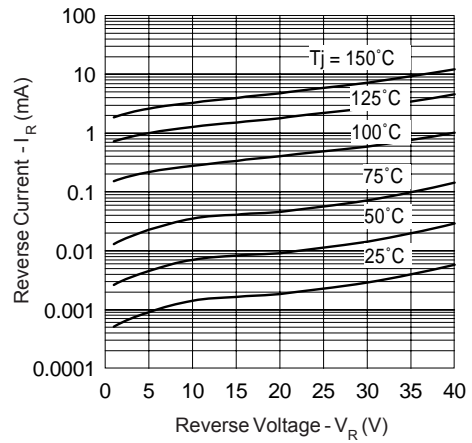


Fig. 2 - Typical Values Of Reverse Current Vs. Reverse Voltage (Per Leg)

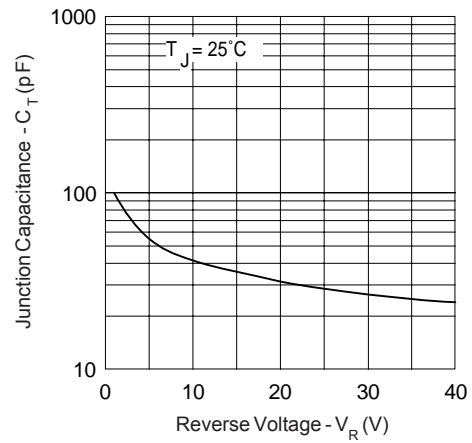


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage (Per Leg)

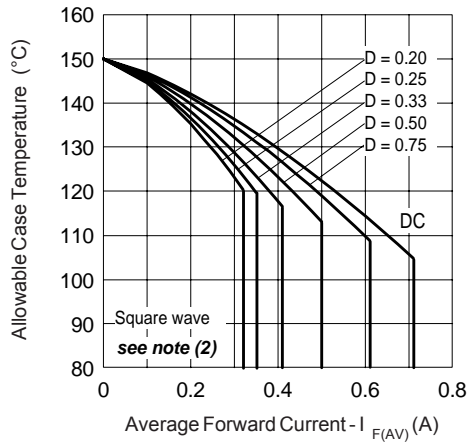


Fig. 4 - Max. Allowable Case Temperature Vs. Average Forward Current

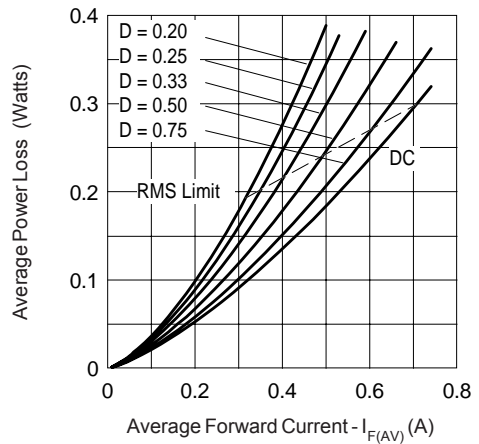


Fig. 5 - Forward Power Loss Characteristics

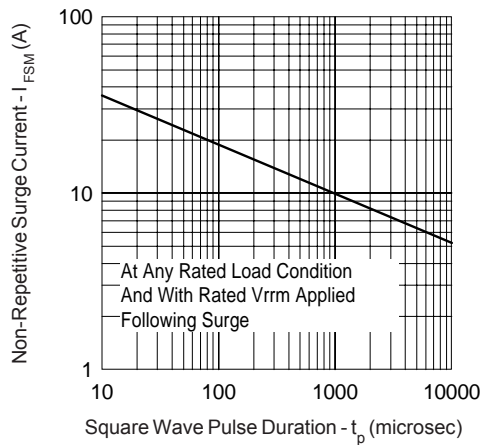
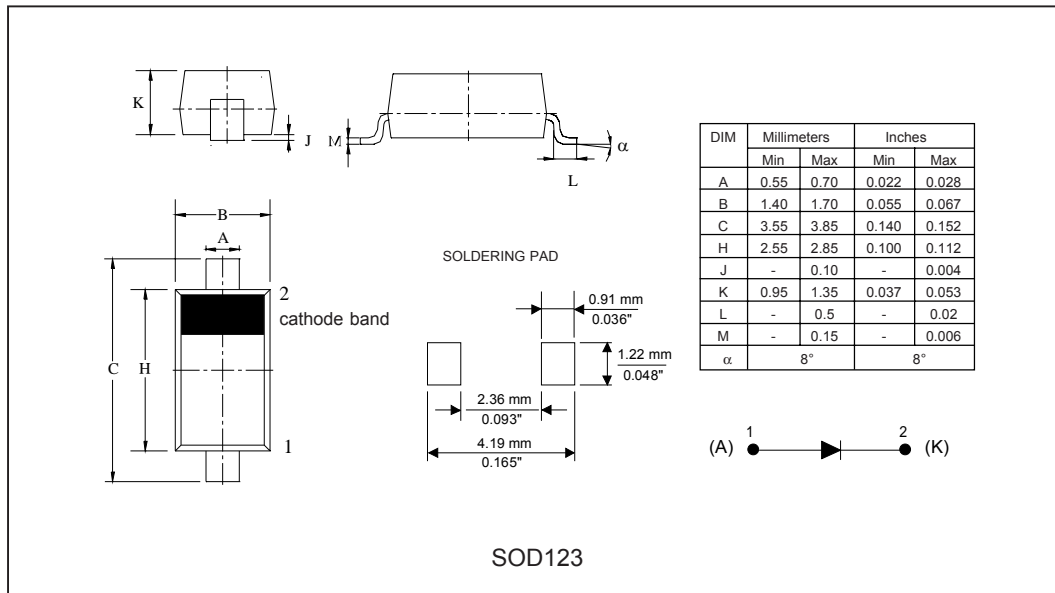


Fig. 6 - Max. Non-Repetitive Surge Current

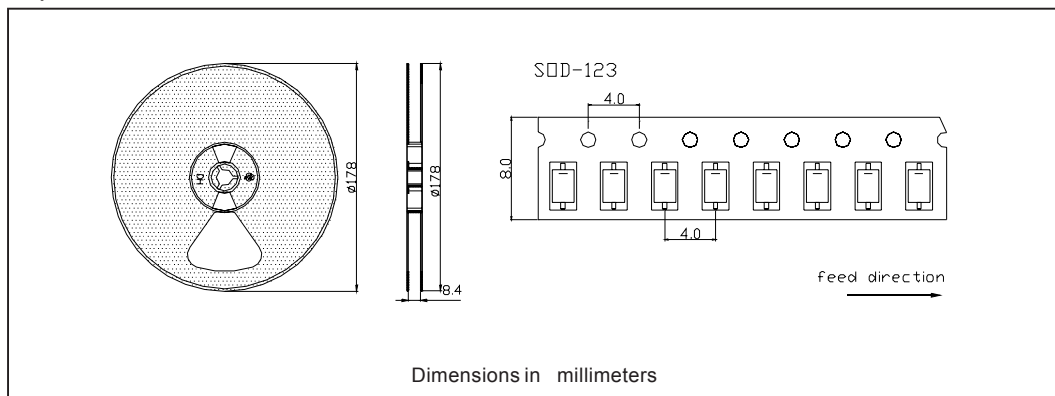
(2) Formula used:  $T_c = T_j - Pd \times R_{thJC}$

Pd = Forward Power Loss =  $I_{F(AV)} \times V_{FM} @ (I_{F(AV)}/D)$  (see Fig. 4)

Outline Table



Tape & Reel Information



Ordering Information Table

Device	Package	Marking	Base qty	Delivery mode
MBR0540	SOD-123	CY <u>W</u> LC	3000	Tape & Reel

MBR0540

Bulletin PD-20203 rev. A 10/06

International  
**IOR** Rectifier

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Data and specifications subject to change without notice.  
This product has been designed and qualified for Industrial Level for Industrial Level.  
Qualification Standards can be found on IR's Web site.

International  
**IOR** Rectifier

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